

WHAT IS CLAIMED IS:

1. A method of fabricating a semiconductor device comprises steps of:
  - forming an active layer over a substrate;
  - forming an insulating film containing silicon on said active layer;
  - exposing a portion of said active layer by removing a part of said insulating film containing silicon;
  - forming a first insulating film over the exposed portion of said active layer;
  - forming a gate wiring and a second capacitance electrode over said insulating film containing silicon and said first insulating film;
  - forming a first interlayer insulating film over said gate wiring and said second capacitance electrode;
  - exposing a portion of said second capacitance electrode by removing a part of said first interlayer insulating film;
  - forming a second dielectric over the exposed portion of said second capacitance electrode;
  - forming a light-shielding film over said first interlayer insulating film and said second dielectric;
  - forming a second interlayer insulating film over said light-shielding film;
  - forming a source wiring or a drain wiring over said second interlayer insulating film;
  - forming a third interlayer insulating film over said source wiring or said drain wiring; and
  - forming a pixel electrode, over said third interlayer insulating film, electrically connected with said light-shielding film and said drain wiring.
2. A method according to claim 1, wherein at least one of said first dielectric and said second dielectric is an insulating film formed by a thermal CVD method and containing silicon.
3. A method according to claim 14, wherein said pixel electrode is an anode or a cathode of an EL element.